


**REMARKS**

Claims 32-35 have been amended to address antecedent basis issues. A marked up version of changes is in Appendix A. Claims 1-40 remain in the application. Examination and consideration of the application, as amended, is hereby requested.

Respectfully Submitted,  
Z. Chen et al

By:   
Timothy F. Myers  
Patent Attorney  
Registration No. 42,919

Hewlett-Packard Company  
Legal Department  
1000 NE Circle Blvd.  
Corvallis, OR 97330  
Telephone: (541)715-4197  
Fax: (541)715-8581

Appendix A  
Marked up changes

32. A focused [metal insulator semiconductor] emitter, comprising:

5       a tunneling layer less than about 500 angstroms in thickness disposed  
on a semiconductor substrate;

          a polymer spacer layer disposed on the semiconductor substrate and  
defining a first opening disposed over the tunneling layer;

          a focusing lens layer disposed on the polymer spacer layer and  
10       defining a second opening disposed over the tunneling layer; and  
          a cathode layer disposed on the tunneling layer.

33. The [electron lens]focused emitter of claim 32 wherein the polymer spacer  
[material]layer is between about 2 microns and about 12 microns thick.

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34. The [electron lens]focused emitter of claim 32 wherein the polymer spacer  
layer has been cured to remove volatile content.

35. An electronic device comprising at least one [electron lens]focused  
20       emitter of claim 32.